



**TO-252-2L Plastic-Encapsulate MOSFETS**

**CCMC03N120 N-Channel Power MOSFET**

V <sub>DS</sub>	R <sub>DS(ON)</sub> (Typ.)	I <sub>D</sub>
1200 V	6.7Ω@10V	3A

**DESCRIPTION**

The CCMC03N120 provides excellent R<sub>DS(ON)</sub> with low gate charge. It can be used in a wide variety of applications.

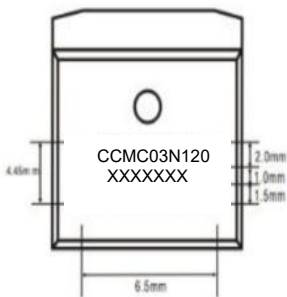
**FEATURES**

- RoHS Compliant
- Low ON Resistance
- Low Gate Charge
- Peak Current vs Pulse Width Curve
- Inductive Switching Curves
- AEC Q101 Qualified

**APPLICATIONS**

- SMPS
- Adaptor
- Electric welder

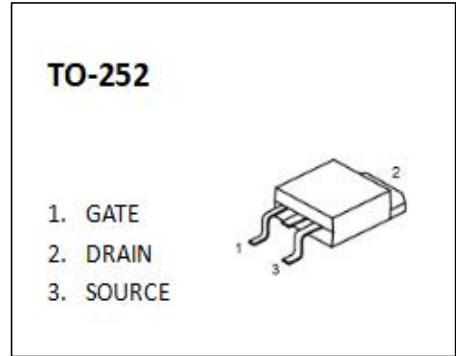
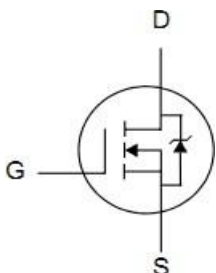
**MARKING**



CCMC03N120 =Part No.

XXXXXXX = Code

**EQUIVALENT CIRCUIT**



**ABSOLUTE MAXIMUM RATINGS( $T_c=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	1200	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Continuous Drain Current $T_c=25^{\circ}\text{C}$	$I_D$	3	A
Continuous Drain Current $T_c=125^{\circ}\text{C}$	$I_D$	1.8	A
Pulsed Drain Current <sup>1</sup>	$I_{DM}$	12	A
Single Pulse Avalanche Energy <sup>2</sup>	EAS	31	mJ
Total Power Dissipation	$P_D$	100	W
Thermal Resistance from Junction to Case <sup>3</sup>	$R_{\theta JC}$	1.5	$^{\circ}\text{C}/\text{W}$
Thermal Resistance from Junction to Ambient <sup>4</sup>	$R_{\theta JA}$	120	$^{\circ}\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~ +175	$^{\circ}\text{C}$
Soldering Temperature , for 10S(1.6mm from case)	-	260	$^{\circ}\text{C}$

## Notes:

- 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2.Start  $T_J = 25^{\circ}\text{C}$ ,  $L = 10\text{mH}$ ,  $I_{AS} = 2.5\text{A}$ ,  $V_{GS} = 10\text{V}$ .
- 3.Water cooled heatsink,  $P_D$  adjusted for a peak junction temperature of  $175^{\circ}\text{C}$ .
- 4.1 cubic foot chamber, free air.

# MOSFET ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise specified

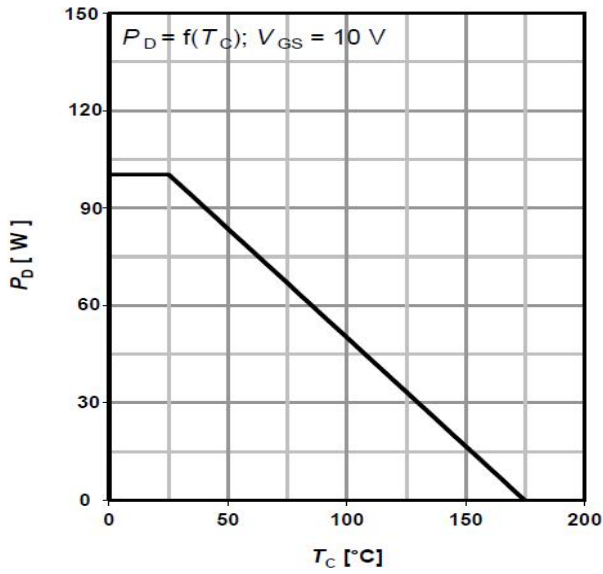
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	1200			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 1200V, V_{GS} = 0V, T_J = 25^\circ C$		1.18	5	$\mu A$
		$V_{DS} = 1200V, V_{GS} = 0V, T_J = 125^\circ C$		1.7	10	
		$V_{DS} = 1200V, V_{GS} = 0V, T_J = 175^\circ C$		35	50	
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 30V, V_{DS} = 0V$			$\pm 100$	nA
<b>On characteristics <sup>1</sup></b>						
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3	3.7	5	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1.5A$		6.7	9	$\Omega$
Transconductance	$g_{fs}$	$V_{DS} = 15V, I_D = 1.5A$		3.8		S
<b>Dynamic characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$		857		$\mu F$
Output Capacitance	$C_{oss}$			59		
Reverse Transfer Capacitance	$C_{rss}$			7.1		
Gate resistance	$R_g$	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		4.2		$\Omega$
<b>Switching characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DD} = 960V, V_{GS} = 10V, I_D = 3A$		19.7		nC
Gate-Source Charge	$Q_{gs}$			7.5		
Gate-Drain Charge	$Q_{gd}$			5.4		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 600V, V_{GS} = 10V, I_D = 3A, R_G = 10\Omega$		15.1		ns
Turn-on rise time	$t_r$			19.4		
Turn-off delay time	$t_{d(off)}$			25.6		
Turn-off fall time	$t_f$			76.2		
<b>Drain-source Diode characteristics <sup>1</sup></b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_{SD} = 3A, T_J = 25^\circ C$			1.5	V
Continuous Source Current	$I_S$	$T_C = 25^\circ C$			3	A
Pulsed drain-source diode forward current	$I_{SM}$	—			12	A
Reverse recovery time	$T_{rr}$	$I_F = 3A, di/dt = 100A/\mu s$		526		ns
Reverse recovery charge	$Q_{rr}$				2000	

Note :

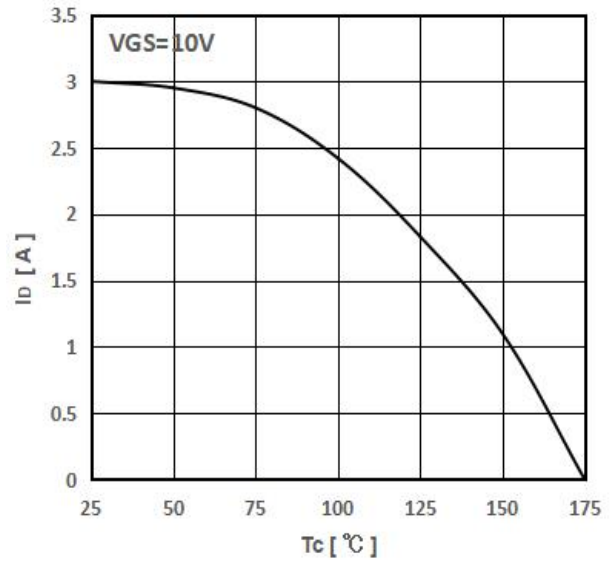
1. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .

# Typical Characteristics

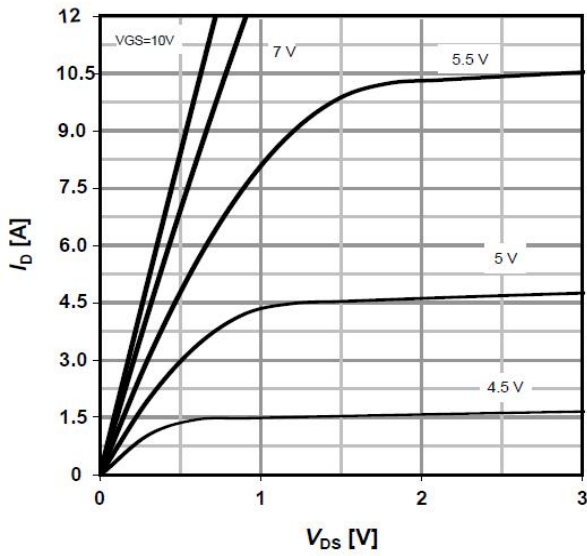
PD -- Tc



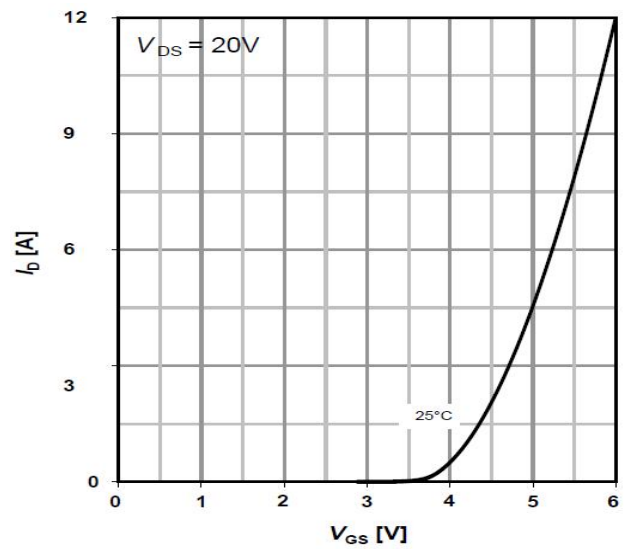
ID -- Tc



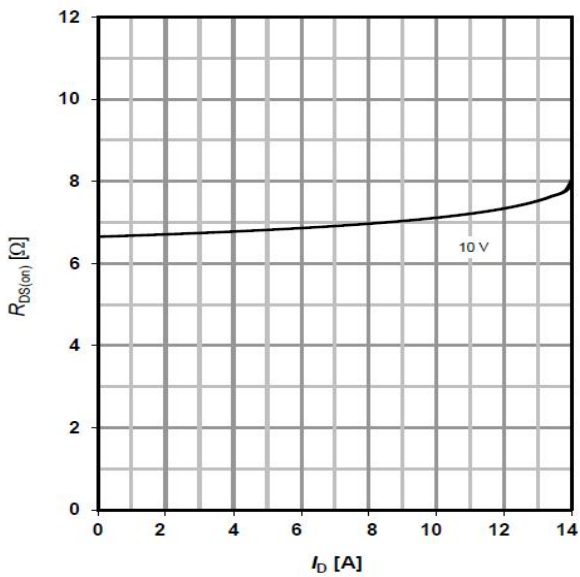
ID -- VDS



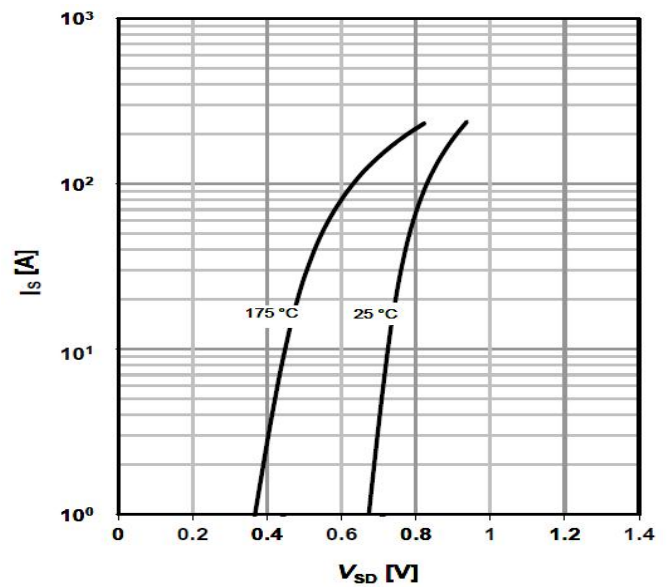
ID -- VGS



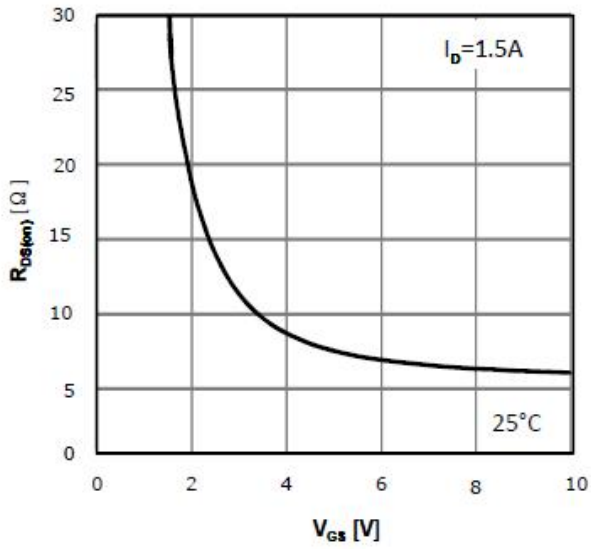
RDS(on) -- ID



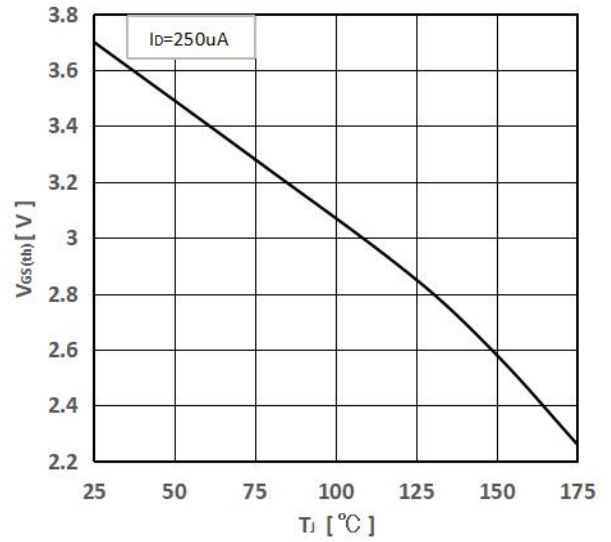
IS -- VSD



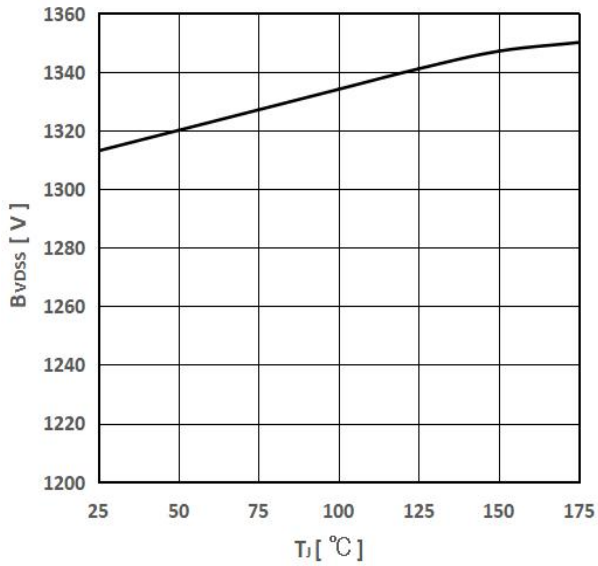
### RDS(on) -- VGS



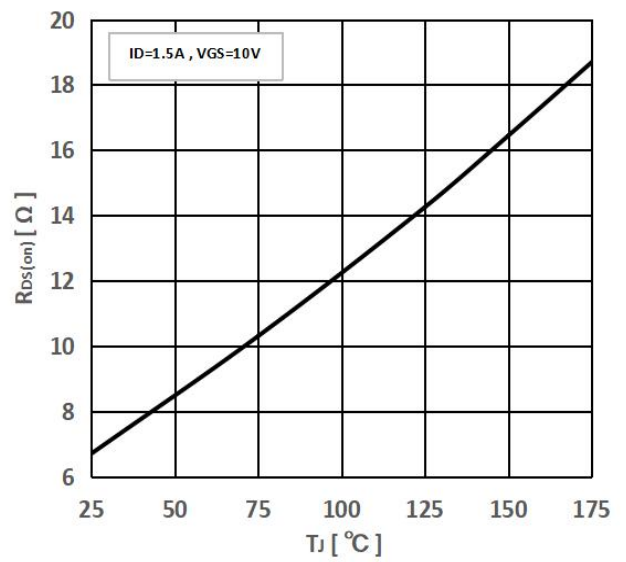
### Threshold Voltage



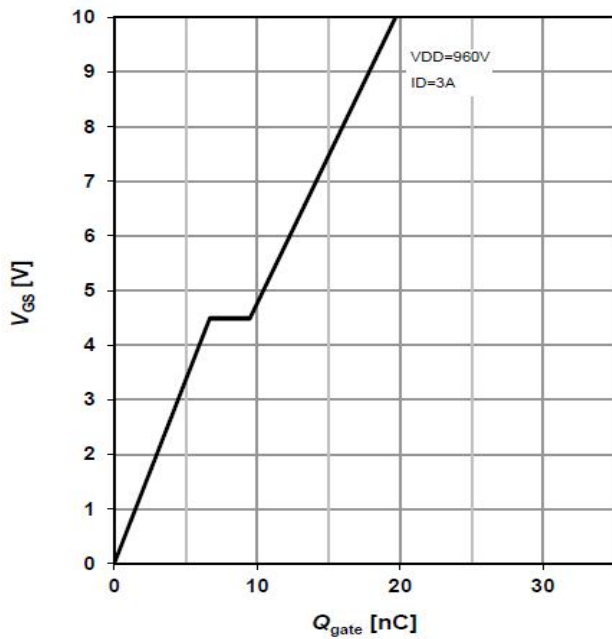
### Drain-source breakdown voltage



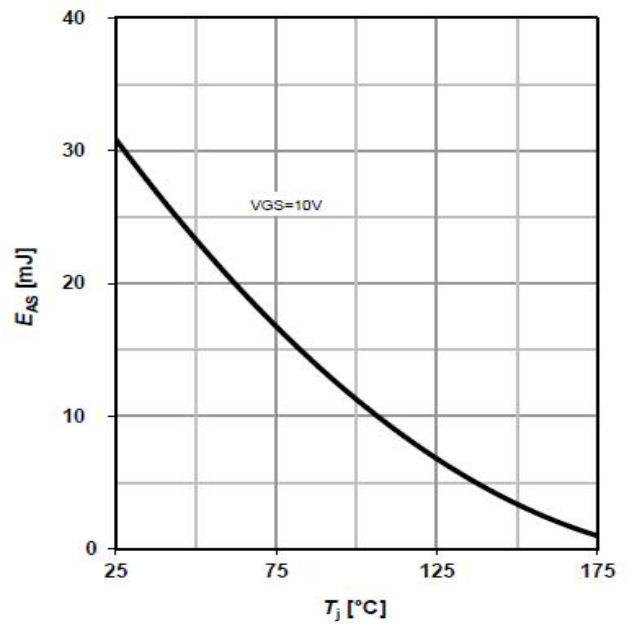
### RDS(on) -- Tj



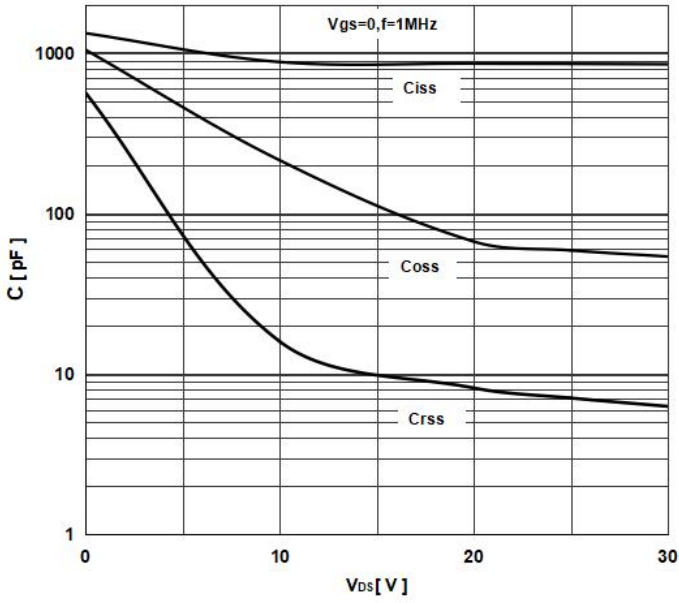
### Typ.gate charge



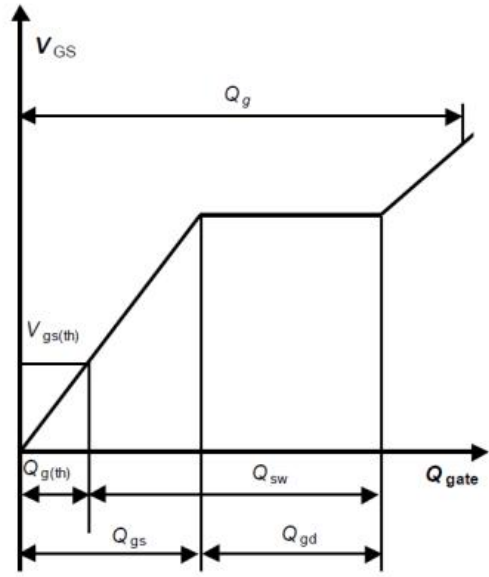
### Avalanche energy



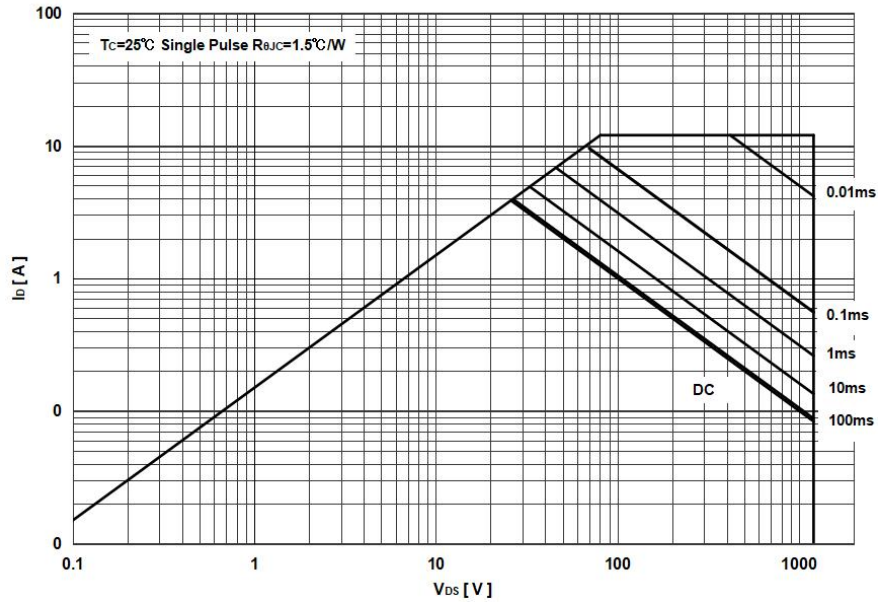
### Typ. capacitance



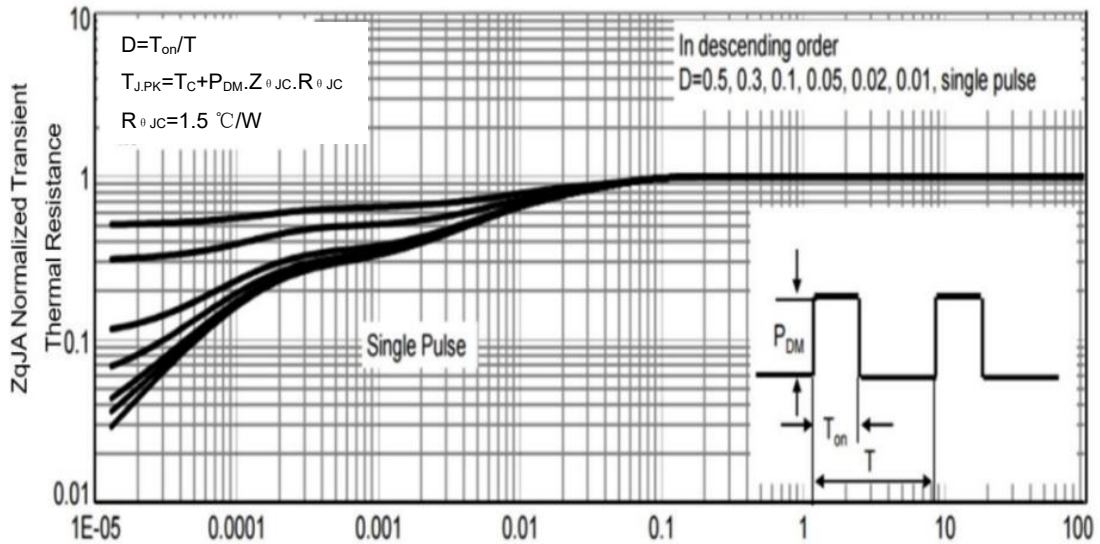
### Gate charge waveforms



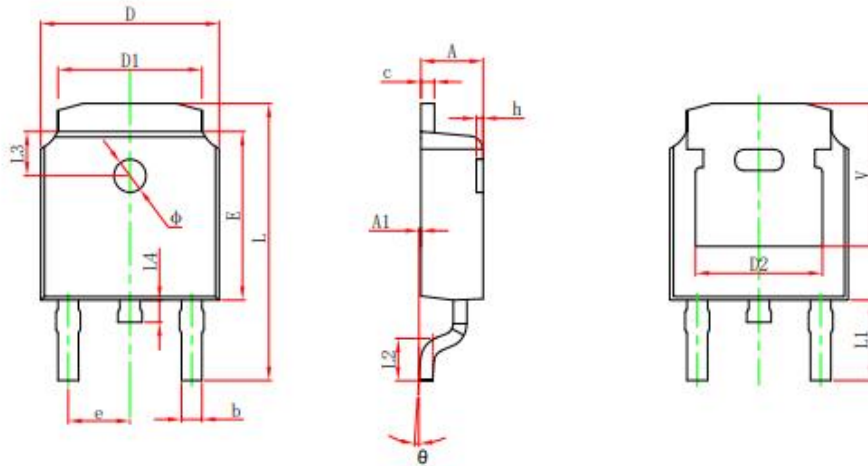
### Maximum Forward Biased Safe Operating Area



### Normalized Thermal Transient Impedance

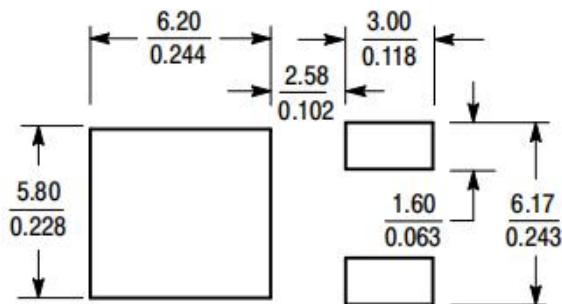


## TO-252 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

## TO-252 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: 0.5mm.
3. The pad layout is for reference purposes only.

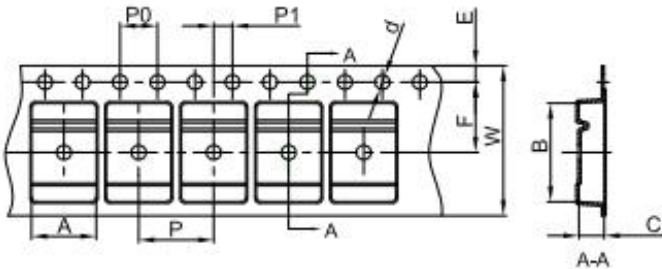
### NOTICE

Cloudchild reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Cloudchild does not assume any liability arising out of the application or use of any product described herein.

ChongQing Cloudchild Technology Co., Ltd. (short for Cloudchild) exerts the greatest possible effort to ensure high quality and reliability. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing Cloudchild products, to comply with the standards of safety in making a safe design for the entire system, including redundancy, fire-prevention measures, and malfunction prevention, to prevent any accidents, fires, or community damage that may ensue. In developing your designs, please ensure that Cloudchild products are used within specified operating ranges as set forth in the most recent Cloudchild products specifications.

## TO-252-2L Tape and Reel

### TO-252 Embossed Carrier Tape

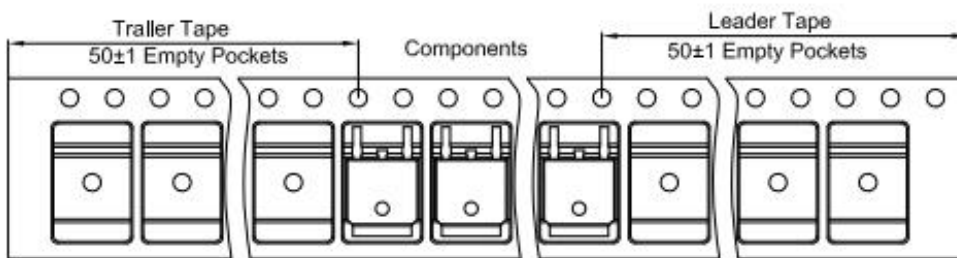


#### Packaging Description:

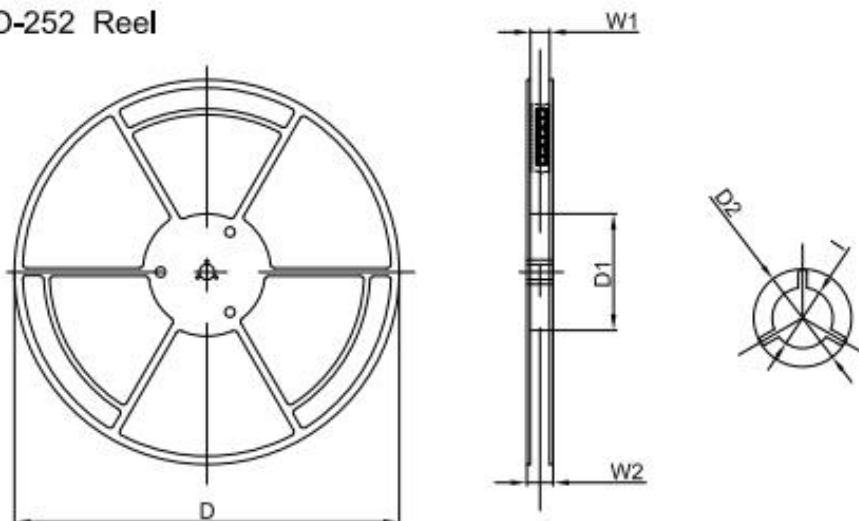
TO-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 25,00 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter											
Pkg type	A	B	C	d	E	F	P0	P	P1	W	
TO-252	6.90	10.50	2.70	Ø1.55	1.75	7.50	4.00	8.00	2.00	16.00	

### TO-252 Tape Leader and Trailer



### TO-252 Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	W1	W2	I
13" Dia	330.00	100.00	Ø21.00	16.40	21.00	Ø13.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13Inch	2,500 pcs	340×336×29	25,000 pcs	353×346×365	



Date of change	Rev #	revise content
2022/11/22	A/0	/